# SENSITRON SEMICONDUCTOR

DATASHEET 5182, REV F.1

# SURFACE MOUNT ULTRAFAST RECTIFIER (MELF)



## DESCRIPTION: 1200 VOLT, 1.0 AMP, 40 NS RECTIFIER IN A SURFACE MOUNT (MELF) PACKAGE

#### **MAXIMUM RATINGS**

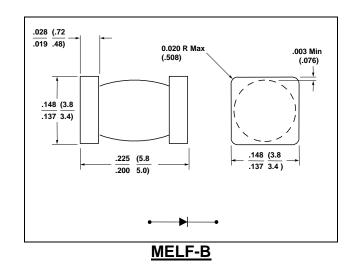
| ALL RATINGS ARE                                 | ALL RATINGS ARE AT TA=25°C UNLESS OTHERWISE SPECIFIED. |      |      |       |  |  |  |  |
|---|--|------|------|-------|--|--|--|--|
| RATING  | SYMBOL   | MIN  | MAX  | UNITS |  |  |  |  |
| BREAKDOWN VOLTAGE                               | V <sub>BR</sub>  | 1200 |      | Volts |  |  |  |  |
| PEAK INVERSE VOLTAGE                            | PIV  |      | 900  | Volts |  |  |  |  |
| MAXIMUM AVERAGE DC OUTPUT CURRENT               | Ι <sub>ο</sub>   |      | 1.0  | Amps  |  |  |  |  |
| PEAK SINGLE CYCLE SURGE CURRENT                 | I <sub>FSM</sub>                                       |      | 40   | Amps  |  |  |  |  |
| (t <sub>p</sub> =8.3 ms, half sine wave)        |  |      |      |       |  |  |  |  |
| MAXIMUM THERMAL RESISTANCE                      | $R_{	ext{	heta}JC}$                                    |      | 10   | °C/W  |  |  |  |  |
| (Junction to end cap)                           |  |      |      |       |  |  |  |  |
| THERMAL IMPEDANCE                               | Z <sub>θJX</sub>                                       |      | 2.5  | °C/W  |  |  |  |  |
| MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE | T <sub>op,sig</sub>                                    | -65  | +175 | °C    |  |  |  |  |

#### **ELECTRICAL CHARACTERISTICS**

| CHARACTERISTIC                      | TEST CONDITIONS                                      | SYMBOL                  | MIN  | TYP  | MAX  | UNITS |
|-------------------------------------|--|-------------------------|------|------|------|-------|
| FORWARD VOLTAGE DROP<br>300µs pulse | IF=0.1 A   | V <sub>F</sub>          |      |      | 1.05 | Volts |
|                                     | IF=0.2 A   | V <sub>F</sub>          |      |      | 1.20 | Volts |
| FORWARD VOLTAGE DROP<br>300µs pulse | T <sub>A</sub> = -55°C, IF=1.0 A                     | V <sub>F</sub>          |      |      | 3.2  | Volts |
|                                     | T <sub>J</sub> =+100°C, IF=0.1 A                     | V <sub>F</sub>          |      | 0.68 | 0.75 | Volts |
| REVERSE CURRENT @ 900V              | T <sub>A</sub> =25°C                                 | I <sub>R</sub>          |      |      | 2.0  | μΑ    |
|                                     | T <sub>A</sub> =100°C                                | I <sub>R</sub>          |      | 20   | 30   | μΑ    |
| BREAKDOWN VOLTAGE                   | I <sub>BR</sub> =50 μA                               | V <sub>BR</sub>         | 1200 |      |      | Volts |
| BREAKDOWN VOLTAGE                   | I <sub>BR</sub> =50 μΑ, Τ <sub>Α</sub> =-55°C        | V <sub>BR</sub>         | 1100 |      |      | Volts |
| REVERSE RECOVERY TIME               | I <sub>F</sub> =500mA, I <sub>R</sub> =1A,           | t <sub>rr</sub> @ 25°C  |      | 35   | 40   | Nsec  |
|                                     | I <sub>RR</sub> =250mA                               | t <sub>rr</sub> @ 100°C |      | 80   | 90   | Nsec  |
| JUNCTION CAPACITANCE                | f=1MHz, V <sub>R</sub> =10V,<br>T <sub>A</sub> =25°C | CJ                      |      | 25   | 30   | pF    |

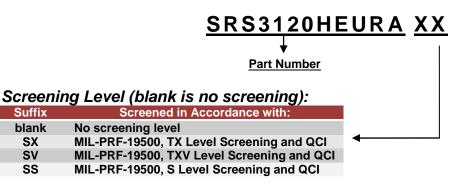
#### SENSITRON **TECHNICAL DATA** DATASHEET 5182, REV F.1

## PACKAGE DIMENSIONS (inches/mm)



Note: The cathode side is marked with a dark colored band on one side of the diode body.

#### PART ORDERING INFORMATION



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